

### ● General Description

The AGM315MN combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

This device is ideal for load switch and battery protection applications.

### ● Features

- Advance high cell density Trench technology
- Low  $R_{DS(ON)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

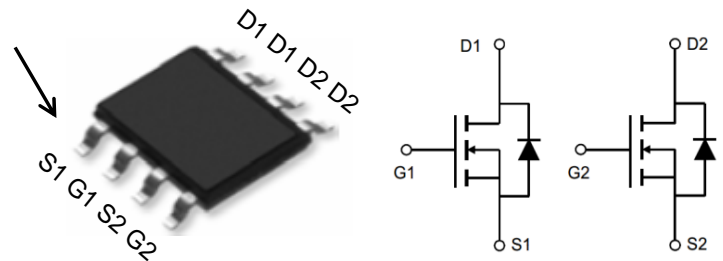
### ● Application

- MB/VGA Vcore
- SMPS 2<sup>nd</sup> Synchronous Rectifier
- POL application
- BLDC Motor driver

### Product Summary

BVDSS	RDS(ON)	ID
30V	12mΩ	12A

### SOP8 Pin Configuration



### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM315MN	AGM315MN	SOP8	330mm	12mm	3000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	30	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Ta=25°C) <b>(Note 1)</b>	12	A
	Drain Current-Continuous(Ta=100°C)	10	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed <b>(Note 2)</b>	50	A
PD	Maximum Power Dissipation(Ta=25°C)	2.5	w
	Maximum Power Dissipation(Ta=100°C)	1.0	w
EAS	Avalanche energy <b>(Note 3)</b>	14	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	---	50	°C/W

**Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>On/Off States</b>						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	30	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=30V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	1.2	1.5	2.5	V
gFS	Forward Transconductance	VDS=5V,ID=8A	--	13	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=11A	--	12	16	mΩ
		VGS=4.5V, ID=8A	--	19	25	mΩ
<b>Dynamic Characteristics</b>						
Ciss	Input Capacitance	VDS=25V,VGS=0V, F=1MHZ	--	345	--	pF
Coss	Output Capacitance		--	55	--	pF
Crss	Reverse Transfer Capacitance		--	32	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	--	--	Ω
<b>Switching Times</b>						
td(on)	Turn-on Delay Time	VDS=15V, ID=1A, RGEN=6Ω	--	2.8	--	nS
tr	Turn-on Rise Time		--	7.2	--	nS
td(off)	Turn-Off Delay Time		--	15.8	--	nS
tf	Turn-Off Fall Time		--	4.6	--	nS
Qg	Total Gate Charge	VGS=4.5V, VDS=15V, ID=8A	--	4.1	--	nC
Qgs	Gate-Source Charge		--	1.0	--	nC
Qgd	Gate-Drain Charge		--	2.1	--	nC
<b>Source-Drain Diode Characteristics</b>						
ISD	Source-Drain Current(Body Diode)		--	--	12	A
VSD	Forward on Voltage	VGS=0V,Is=11A	--	--	1.2	V
trr	Reverse Recovery Time	IF=11A , di/dt=100A/μs , TJ=25°C	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C

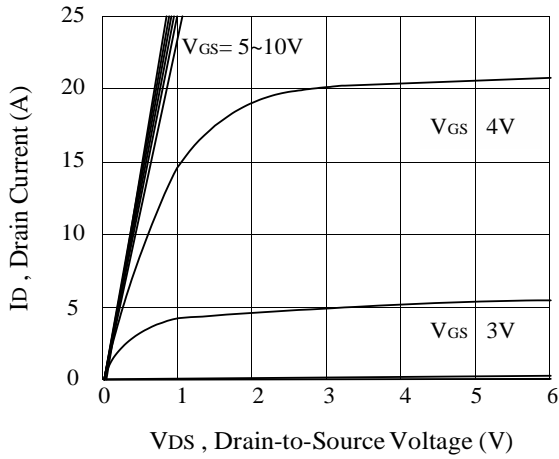


Figure 1. Output Characteristics

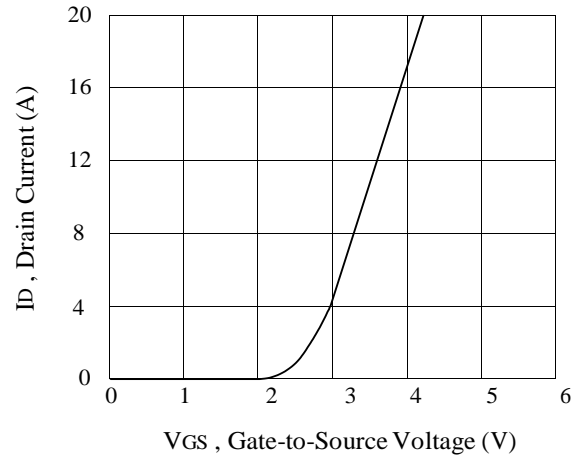


Figure 2. Transfer Characteristics

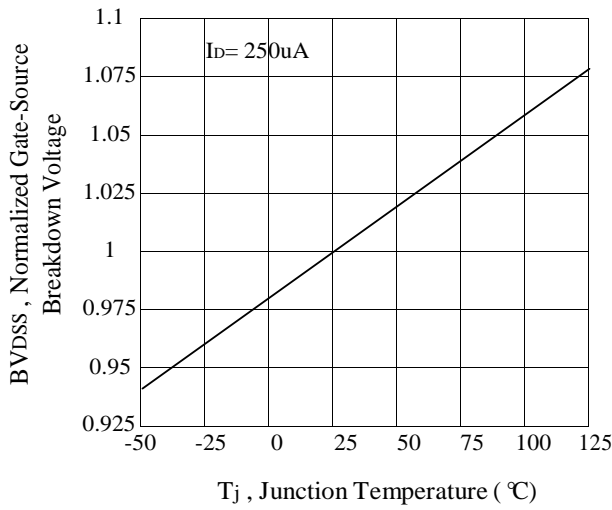


Figure 3. Breakdown Voltage Variation with Temperature

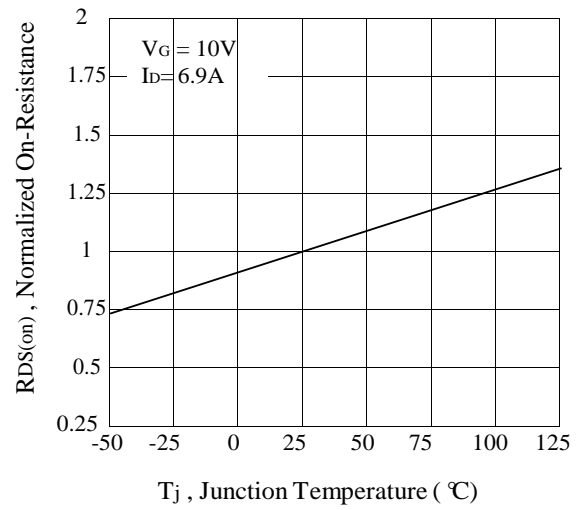


Figure 4. On-Resistance Variation with Temperature

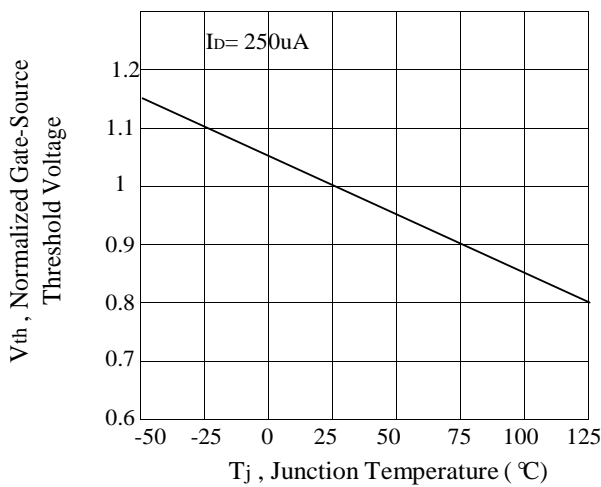


Figure 5. Gate Threshold Variation with Temperature

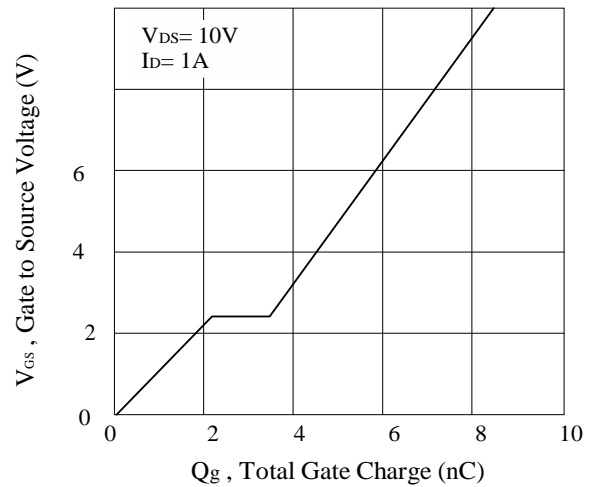
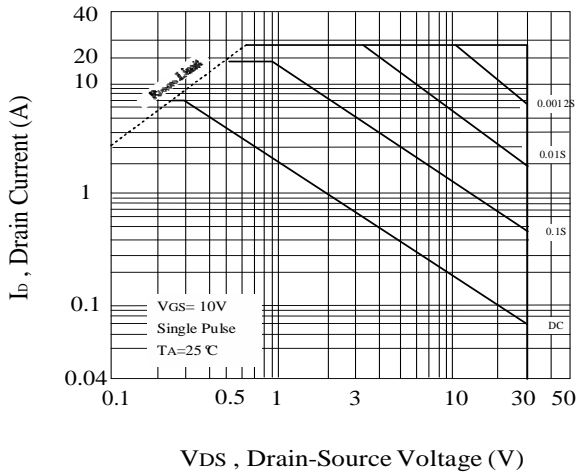
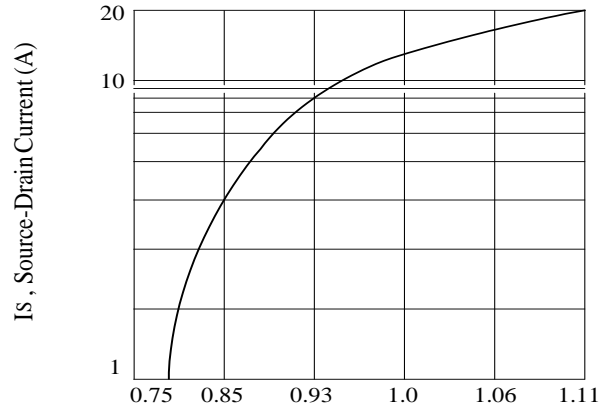


Figure 6. Gate Charge



VDS, Drain-Source Voltage (V)  
Figure 7. Maximum Safe Operating Area



VSD, Body Diode Forward Voltage (V)  
Figure 8. Body Diode Forward Voltage Variation with Source Current

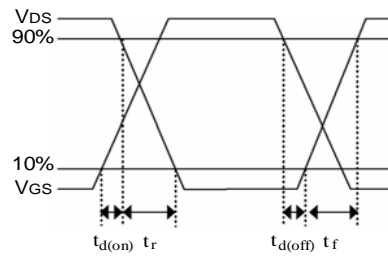
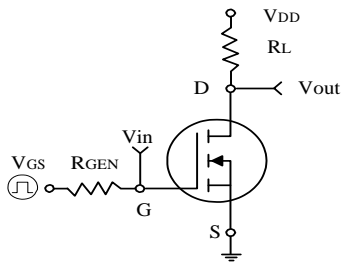


Figure 9. Switching Test Circuit and Switching Waveforms

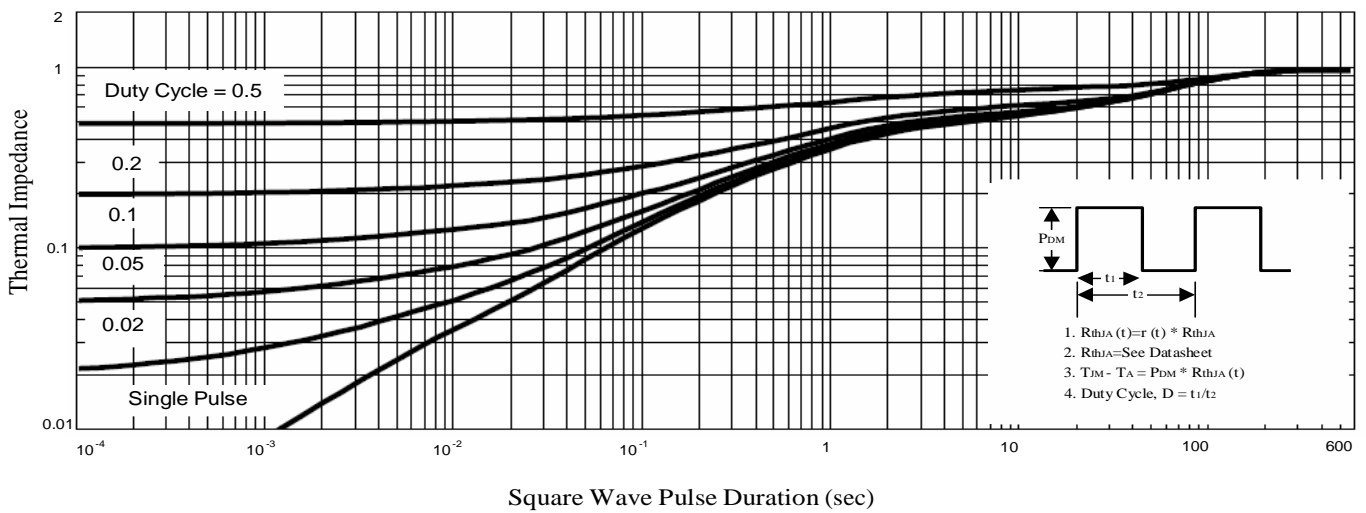
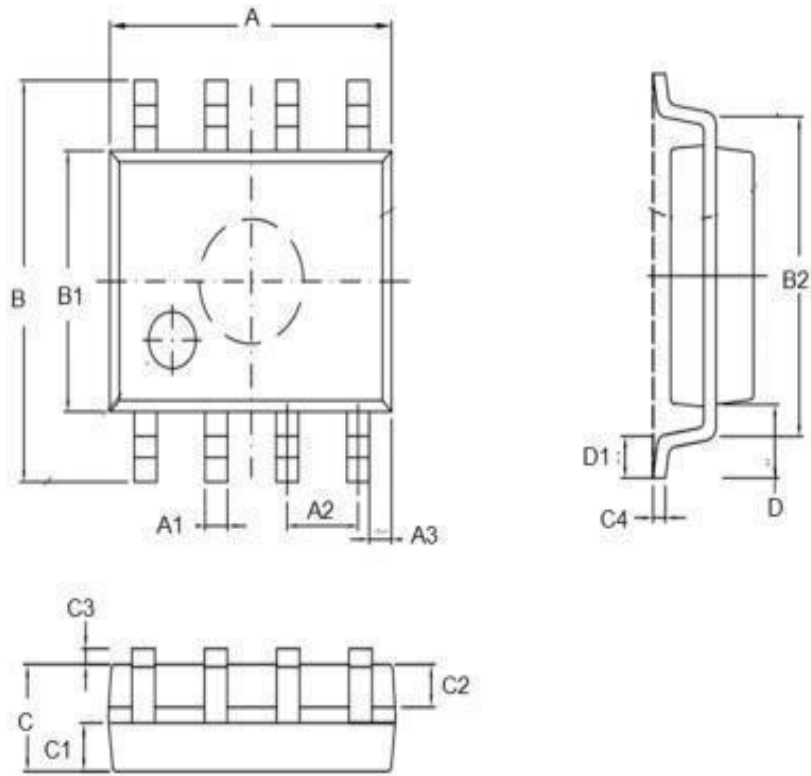


Figure 10. Normalized Thermal Transient Impedance Curve

**•Dimensions(SOP8)**

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.00	C	1.30		1.50
A1	0.37		0.47	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.19	0.20	0.23
B1	3.80		4.00	D		1.05	
B2		5.00		D1	0.40		0.62




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